捷多邦,专业PCB打样工 T278V512

Features

- WWW.DZSC.COM Fast Read Access Time - 90 ns
- **Dual Voltage Range Operation** Unregulated Battery Power Supply Range, 2.7V to 3.6V or Standard 5V ± 10% Supply Range
- Pin Compatible with JEDEC Standard AT27C512
- Low Power CMOS Operation
 - 20 μ A max. (less than 1 μ A typical) Standby for V_{CC} = 3.6V 29 mW max. Active at 5 MHz for V_{CC} = 3.6V
- JEDEC Standard Surface Mount Packages DZSC.COM 32-Lead PLCC
 - 28-Lead 330-mil SOIC
 - 28-Lead TSOP
- High Reliability CMOS Technology 2.000V ESD Protection 200 mA Latchup Immunity
- Rapid[™] Programming Algorithm 100 µs/byte (typical)
- CMOS and TTL Compatible Inputs and Outputs JEDEC Standard for LVTTL and LVBO
- Integrated Product Identification Code
- **Commercial and Industrial Temperature Ranges**

Description

Note: PLCC Package Pins 1 and

7 are DON'T CONNECT.

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The AT27BV512 is a high performance, low power, low voltage 524,288 bit one-time programmable read only memory (OTP EPROM) organized as 64K by 8 bits. It requires only one supply in the range of 2.7V to 3.6V in normal read mode operation, making it ideal for fast, portable systems using either regulated or unregulated battery power.

Atmel's innovative design techniques provide fast speeds that rival 5V parts while keeping the low power consumption of a 3V supply. At $V_{CC} = 2.7V$, any byte can be accessed in less than 90 ns. With a typical power consumption of only 18 mW at 5 MHz and $V_{CC} = 3V$, the AT27BV512 consumes less than one fifth the power of a standard 5V EPROM.

(continued) **Pin Configurations** SOIC Top View Pin Name Function VCC A14 A13 A8 A9 A15 A12 A7 A6 28 27 A0 - A15 Addresses 3 26 4 25 00 - 07 Outputs A5 □ A4 □ 5 6 24 A9 A11 OE/VPP A10 CE 07 23 CE Chip Enable A3 22 A2 A1 A0 8 21 OE/VPP Output Enable 9 20 10 19 NC No Connect 06 05 04 03 00 □ 11 18 01 17 12 PLCC Top View 02 13 16 GND C 15 14 A7 A15 VCC A13 A12 NC A14 32 30 2 **TSOP** Top View 31 29 A6 A5 28 Α9 Type 1 A4 27 A11 A9 A11 A10 A3 26 NC 22 21 23 20 CE A2 25 OE/VPP 24 07 19 A8 25 18 06 24 A1 10 <u>A10</u> 26 A13 17 O5 23 A0 11 CE 04 27 16 A14 22 07 vcc О3 NC 12 A12 A15 28 15 14 GND 00 21 06 13 15 17 19 2 13 02 16 18 12 20 3 01 A6 4 11 00 Α5 5 10 A0 O2 NC O4 Α4 6 9 Δ1 O1 GND O3 O5 8 A2 A3



512K (64K x 8) Unregulated Battery-Voltage **High Speed** OTP CMOS EPROM









Description (Continued)

Standby mode supply current is typically less than 1 μ A at 3V. The AT27BV512 simplifies system design and stretches battery lifetime even further by eliminating the need for power supply regulation.

The AT27BV512 is available in industry standard JEDECapproved one-time programmable (OTP) plastic PLCC, SOIC, and TSOP packages. All devices feature two-line control (CE, OE) to give designers the flexibility to prevent bus contention.

The AT27BV512 operating with V_{CC} at 3.0V produces TTL level outputs that are compatible with standard TTL logic devices operating at V_{CC} = 5.0V. At V_{CC} = 2.7V, the part is compatible with JEDEC approved low voltage battery operation (LVBO) interface specifications. The device is also capable of standard 5-volt operation making it ideally suited for dual supply range systems or card products that are pluggable in both 3-volt and 5-volt hosts.

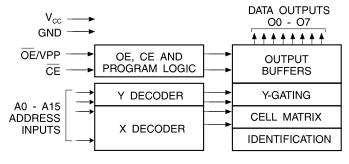
Atmel's AT27BV512 has additional features to ensure high quality and efficient production use. The RapidTM Programming Algorithm reduces the time required to program the part and guarantees reliable programming. Programming time is typically only 100 µs/byte. The Integrated Product Identification Code electronically identifies the device and manufacturer. This feature is used by industry standard programming equipment to select the proper programming algorithms and voltages. The AT27BV512 programs exactly the same way as a standard 5V AT27C512R and uses the same programming equipment.

System Considerations

Switching between active and standby conditions via the Chip Enable pin may produce transient voltage excursions. Unless accommodated by the system design, these transients may exceed data sheet limits, resulting in device non-conformance. At a minimum, a 0.1 μ F high frequency, low inherent inductance, ceramic capacitor should be utilized for each device. This capacitor should be connected between the V_{CC} and Ground terminals of the device, as close to the device as possible. Additionally, to stabilize the supply voltage level on printed circuit boards with large EPROM arrays, a 4.7 μ F bulk electrolytic capacitor should be utilized, again connected between the V_{CC} and Ground terminals. This capacitor should be positioned as close as possible to the point where the power supply is connected to the array.

AT27BV512

Block Diagram



Absolute Maximum Ratings*

Temperature Under Bias	40°C to +85°C
Storage Temperature	65°C to +125°C
Voltage on Any Pin with Respect to Ground	2.0V to +7.0V ⁽¹⁾
Voltage on A9 with Respect to Ground	2.0V to +14.0V ⁽¹⁾
VPP Supply Voltage with Respect to Ground	2.0V to +14.0V ⁽¹⁾

*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Note: 1. Minimum voltage is -0.6V dc which may undershoot to -2.0V for pulses of less than 20 ns. Maximum output pin voltage is V_{CC} + 0.75V dc which may be exceeded if certain precautions are observed (consult application notes) and which may overshoot to +7.0V for pulses of less than 20 ns.

Operating Modes

Mode \ Pin	CE	OE/V _{PP}	Ai	Vcc	Outputs
Read ⁽²⁾	VIL	VIL	Ai	Vcc (2)	Dout
Output Disable (2)	VIL	Vih	X ⁽¹⁾	Vcc (2)	High Z
Standby ⁽²⁾	VIH	Х	Х	Vcc (2)	High Z
Rapid Program ⁽³⁾	VIL	VPP	Ai	Vcc ⁽³⁾	D _{IN}
PGM Verify ⁽³⁾	VIL	VIL	Ai	Vcc ⁽³⁾	Dout
PGM Inhibit ⁽³⁾	VIH	VPP	Х	V _{CC} ⁽³⁾	High Z
Product Identification ^(3, 5)	VIL	V _{IL}	$A9 = V_{H} {}^{(4)}$ $A0 = V_{IH} \text{ or } V_{IL}$ $A1 - A15 = V_{IL}$	Vcc ⁽³⁾	Identification Code

Notes: 1. X can be V_{IL} or V_{IH} .

- 2. Read, output disable, and standby modes require, $2.7V \le V_{CC} \le 3.6V$, or $4.5V \le V_{CC} \le 5.5V$.
- 3. Refer to Programming Characteristics. Programming modes require $V_{CC} = 6.5V$.

4. $V_H = 12.0 \pm 0.5 V$.

5. Two identifier bytes may be selected. All Ai inputs are held low (V_{IL}), except A9 which is set to V_H and A0 which is toggled low (V_{IL}) to select the Manufacturer's Identification byte and high (V_{IH}) to select the Device Code byte.





DC and AC Operating Conditions for Read Operation

			AT27BV512					
		-90	-12	-15				
Operating Temperature	Com.	0°C - 70°C	0°C - 70°C	0°C - 70°C				
(Case)	Ind.	-40°C - 85°C	-40°C - 85°C	-40°C - 85°C				
Marc Davida Overali		2.7V to 3.6V	2.7V to 3.6V	2.7V to 3.6V				
Vcc Power Supply		5V ± 10%	$5V \pm 10\%$	5V ± 10%				

DC and Operating Characteristics for Read Operation

Symbol	Parameter	Condition	Min	Max	Units
$V_{CC} = 2$.7V to 3.6V				
ILI	Input Load Current	$V_{IN} = 0V$ to V_{CC}		±1	μA
Ilo	Output Leakage Current	Vout = 0V to Vcc		±5	μA
I _{PP1} ⁽²⁾	VPP (1) Read/Standby Current	VPP = VCC		10	μA
laa	V _{CC} ⁽¹⁾ Standby Current	I_{SB1} (CMOS), $\overline{CE} = V_{CC} \pm 0.3V$		20	μA
I _{SB}		I _{SB2} (TTL), \overline{CE} = 2.0 to V _{CC} + 0.5V		100	μA
lcc	Vcc Active Current	$f = 5 \text{ MHz}, I_{OUT} = 0 \text{ mA}, \overline{CE} = V_{IL}, V_{CC} =$	3.6V	8	mA
Ma		V _{CC} = 3.0 to 3.6V	-0.6	0.8	V
VIL	Input Low Voltage	V _{CC} = 2.7 to 3.6V	-0.6	0.2 x V _{CC}	V
Mar .	Input Lligh Voltage	V _{CC} = 3.0 to 3.6V	2.0	V _{CC} + 0.5	V
VIH	Input High Voltage	Vcc = 2.7 to 3.6V	0.7 x Vcc	Vcc + 0.5	V
		I _{OL} = 2.0 mA		0.4	V
Vol	Output Low Voltage	I _{OL} = 100 μA		0.2	V
		I _{OL} = 20 μA		0.1	V
		I _{OH} = -2.0 mA	2.4		V
VOH	Output High Voltage	I _{OH} = -100 μA	V _{CC} - 0.2		V
		I _{OH} = -20 μA	Vcc - 0.1		V
$V_{CC} = 4$.5V to 5.5V				
ILI	Input Load Current	$V_{IN} = 0V$ to V_{CC}		±1	μA
ILO	Output Leakage Current	$V_{OUT} = 0V$ to V_{CC}		±5	μA
I _{PP1} ⁽²⁾	V _{PP} ⁽¹⁾ Read/Standby Current	$V_{PP} = V_{CC}$		10	μΑ
	V _{CC} ⁽¹⁾ Standby Current	I_{SB1} (CMOS), $\overline{CE} = V_{CC} \pm 0.3V$		100	μA
ISB		I_{SB2} (TTL), \overline{CE} = 2.0 to V _{CC} + 0.5V		1	mA
lcc	V _{CC} Active Current	$f = 5 \text{ MHz}, I_{OUT} = 0 \text{ mA}, \overline{CE} = V_{IL}$		20	mA
VIL	Input Low Voltage		-0.6	0.8	V
Viн	Input High Voltage		2.0	Vcc + 0.5	V
Vol	Output Low Voltage	l _{OL} = 2.1 mA		0.4	V
Vон	Output High Voltage	I _{OH} = -400 μA	2.4		V

Notes: 1. $\frac{V_{CC}}{OE}$ must be applied simultaneously with or before $\frac{OE}{OE}/V_{PP}$, and removed simultaneously with or after OE/V_{PP} .

2. V_PP may be connected directly to V_{CC}, except during programming. The supply current would then be the sum of I_{CC} and I_{PP}.

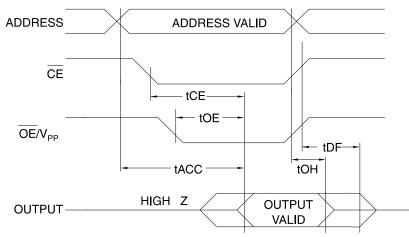
AT27BV512

AC Characteristics for Read Operation ($V_{CC} = 2.7V$ to 3.6V and 4.5V to 5.5V)

			AT27BV512						
			-9	90	-'	12	-*	15	
Symbol	Parameter	Condition	Min	Max	Min	Max	Min	Max	Units
tACC ⁽³⁾	Address to Output Delay	$\overline{CE} = \overline{OE}/V_{PP} = V_{IL}$		90		120		150	ns
tce (2)	CE to Output Delay	$\overline{OE/V_{PP}} = V_{IL}$		90		120		150	ns
t _{OE} ^(2, 3)	OE/V _{PP} to Output Delay	$\overline{CE} = V_{IL}$		50		50		60	ns
t _{DF} ^(4, 5)	OE/VPP or CE High to Output Float, whichever occurred first			40		40		50	ns
tOH	Output Hold from Address, CE or OE/VPP, whichever occurred first		0		0		0		ns

Notes: 2, 3, 4, 5. - see AC Waveforms for Read Operation.

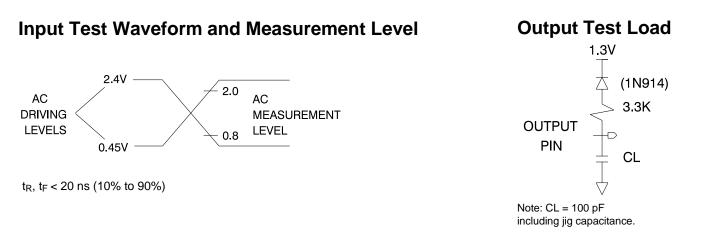
AC Waveforms for Read Operation ⁽¹⁾



- Notes: 1. Timing measurement references are 0.8V and 2.0V. Input AC drive levels are 0.45V and 2.4V, unless otherwise specified.
 - 2. OE/V_{PP} may be delayed up to t_{CE} t_{OE} after the falling edge of CE without impact on t_{CE}.
 - OE/V_{PP} may be delayed up to t_{ACC} t_{OE} after the address is valid without impact on t_{ACC}.
- 4. This parameter is only sampled and is not 100% tested.
- 5. Output float is defined as the point when data is no longer driven.
- 6. When reading the 27BV512, a 0.1 μ F capacitor is required across V_{CC} and grond to supress spurious voltage transients.







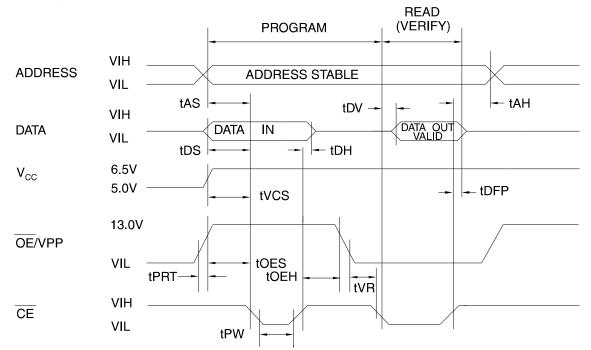
Pin Capacitance (f = 1 MHz, T = 25° C)⁽¹⁾

	Тур	Max	Units	Conditions	
CIN	4	6	pF	$V_{IN} = 0V$	
COUT	8	12	pF	$V_{OUT} = 0V$	

Note: 1. Typical values for nominal supply voltage. This parameter is only sampled and is not 100% tested.

AT27BV512

Programming Waveforms⁽¹⁾



- Notes: 1. The Input Timing Reference is 0.8V for V_{IL} and 2.0V for $V_{\text{IH}}.$
 - 2. t_{OE} and t_{DFP} are characteristics of the device but must be accommodated by the programmer.
- 3. When programming the 27BV512, a 0.1 μF capacitor is required across V_{PP} and ground to supress spurious voltage transients.

DC Programming Characteristics

 T_{A} = 25 $\pm~$ 5°C, V_{CC} = 6.5 $\pm~$ 0.25V, $\overline{\text{OE}}/V_{\text{PP}}$ = 13.0 $\pm~$ 0.25V

		Test			
Symbol	Parameter	Conditions	Min	Max	Units
ILI	Input Load Current	$V_{\text{IN}} = V_{\text{IL}}, V_{\text{IH}}$		±10	μA
VIL	Input Low Level		-0.6	0.8	V
VIH	Input High Level		2.0	V _{CC} + 0.5	V
Vol	Output Low Voltage	I _{OL} = 2.1 mA		0.4	V
Vон	Output High Voltage	I _{OH} = -400 μA	2.4		V
ICC2	V _{CC} Supply Current (Program and Verify)			25	mA
IPP2	OE/VPP Current	$\overline{CE} = V_{IL}$		25	mA
VID	A9 Product Identification Voltage		11.5	12.5	V





AC Programming Characteristics

 $T_{\text{A}} = 25 \pm 5^{\circ}\text{C}, V_{\text{CC}} = 6.5 \pm 0.25\text{V}, \overline{\text{OE}}/\text{V}_{\text{PP}} = 13.0 \pm 0.25\text{V}$

Sym-	Test Conditions* ⁽¹⁾	Liı	nits	
bol	Parameter	Min	Max	Units
tAS	Address Setup Time	2		μS
toes	OE/V _{PP} Setup Time	2		μS
toeh	OE/V _{PP} Hold Time	2		μS
t _{DS}	Data Setup Time	2		μS
t _{AH}	Address Hold Time	0		μS
tDH	Data Hold Time	2		μS
tDFP	CE High to Out- put Float Delay ⁽²⁾	0	130	ns
tvcs	V _{CC} Setup Time	2		μS
tpw	$\overline{\text{CE}}$ Program Pulse Width ⁽³⁾	95	105	μS
tDV	Data Valid from $\overline{CE}^{(2)}$		1	μS
t _{VR}	OE/V _{PP} Recovery Time	2		μS
tPRT	OE/V _{PP} Pulse Rise Time During Programming	50		ns

*AC Conditions of Test:

Input Rise and Fall Times (10% to 90)......20 ns Input Pulse Levels.....0.45V to 2.4V Input Timing Reference Level.....0.8V to 2.0V Output Timing Reference Level.....0.8V to 2.0V

- Notes: 1. $\frac{V_{CC}}{OE}$ must be applied simultaneously or before $\frac{\overline{OE}}{OE}$ /V_{PP} and removed simultaneously or after \overline{OE} /V_{PP}.
 - This parameter is only sampled and is not 100% tested. Output Float is defined as the point where data is no longer driven — see timing diagram.
 - 3. Program Pulse width tolerance is 100 $\mu sec \pm 5\%.$

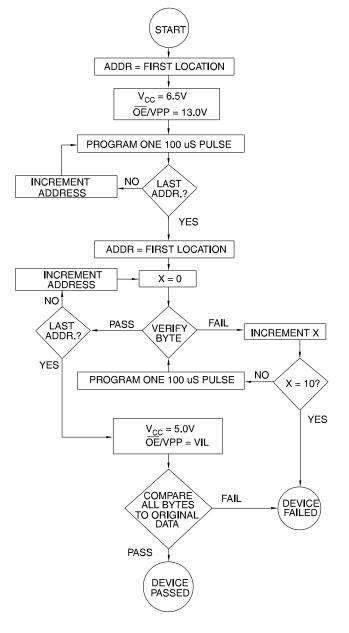
Atmel's 27BV512 Integrated Product Identification Code (1)

		Pins					Hex			
Codes	A0	07	O6	O5	O4	O3	O2	01	00	Data
Manufacturer	0	0	0	0	1	1	1	1	0	1E
Device Type	1	0	0	0	0	1	1	0	1	0D

Note: 1. The AT27BV512 has the same Product Identification Code as the AT27C512R. Both are programming compatible.

Rapid Programming Algorithm

A 100 μ s \overline{CE} pulse width is used to program. The address is set to the first location. V_{CC} is raised to 6.5V and \overline{OE}/V_{PP} is raised to 13.0V. Each address is first programmed with one 100 μ s \overline{CE} pulse without verification. Then a verification / reprogramming loop is executed for each address. In the event a byte fails to pass verification, up to 10 successive 100 μ s pulses are applied with a verification after each pulse. If the byte fails to verify after 10 pulses have been applied, the part is considered failed. After the byte verifies properly, the <u>next</u> address is selected until all have been checked. \overline{OE}/V_{PP} is then lowered to V_{IL} and V_{CC} to 5.0V. All bytes are read again and compared with the original data to determine if the device passes or fails.



Ordering Information

tACC	lcc	(mA)	Ordering Code	Deekage	Operation Banga
(ns)	Active	Standby	Ordering Code	Package	Operation Range
90	8	0.02	AT27BV512-90JC AT27BV512-90RC AT27BV512-90TC	32J 28R 28T	Commercial (0°C to 70°C)
	8	0.02			Industrial (-40°C to 85°C)
120	8	0.02	AT27BV512-12JC AT27BV512-12RC AT27BV512-12TC	32J 28R 28T	Commercial (0°C to 70°C)
	8	0.02	AT27BV512-12JI AT27BV512-12RI AT27BV512-12TI	32J 28R 28T	Industrial (-40°C to 85°C)
150	8	0.02	AT27BV512-15JC AT27BV512-15RC AT27BV512-15TC	32J 28R 28T	Commercial (0°C to 70°C)
	8	0.02	AT27BV512-15JI AT27BV512-15RI AT27BV512-15TI	32J 28R 28T	Industrial (-40°C to 85°C)

	Package Type			
32J	32 Lead, Plastic J-Leaded Chip Carrier (PLCC)			
28R	28 Lead, 0.330" Wide, Plastic Gull Wing Small Outline (SOIC)			
28T	28 Lead, Thin Small Outline Package (TSOP)			

